

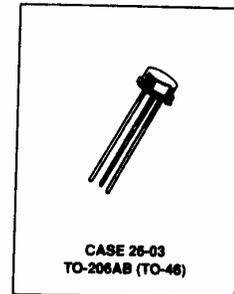
# SEMICONDUCTOR TECHNICAL DATA

**2N5581**  
**2N5582**

**NPN Silicon**  
**Small-Signal Transistors**

**CRYSTALONCS**  
2805 Veterans Highway  
Suite 14  
Ronkonkoma, N.Y. 11776

MAXIMUM RATINGS			
Rating	Symbol	Value	Unit
Collector-Emitter Voltage	V <sub>CEO</sub>	50	V <sub>dc</sub>
Collector-Base Voltage	V <sub>CBO</sub>	75	V <sub>dc</sub>
Collector Current	I <sub>C</sub>	800	mAdc
Device Dissipation	P <sub>T</sub>		
@ T <sub>A</sub> = 25°C		500	mW
Derate above 25°C		2.28	mW/°C
@ T <sub>C</sub> = 25°C		2.0	Watts
Derate above 25°C		11.43	mW/°C
Storage Temperature	T <sub>stg</sub>	-65 to 200	°C



ELECTRICAL CHARACTERISTICS (T <sub>A</sub> = 25°C unless otherwise noted.)				
Characteristic	Symbol	Min	Max	Unit
<b>OFF CHARACTERISTICS</b>				
Collector-Emitter Breakdown Voltage <sup>(1)</sup> (I <sub>C</sub> = 10 mAdc)	V <sub>(BR)CEO</sub>	50	—	V <sub>dc</sub>
Collector-Base Breakdown Voltage (I <sub>C</sub> = 10 μAdc)	V <sub>(BR)CBO</sub>	75	—	V <sub>dc</sub>
Collector Cutoff Current (V <sub>CB</sub> = 60 Vdc)	I <sub>CBO</sub>	—	10	nAdc
(V <sub>CB</sub> = 60 Vdc, T <sub>A</sub> = 150°C)		—	10	μAdc
Emitter Cutoff Current (V <sub>EB</sub> = 4.0 Vdc)	I <sub>EBO</sub>	—	10	nAdc
(V <sub>EB</sub> = 6.0 Vdc)		—	10	μAdc

<sup>1)</sup> Pulsed. Pulse Width 250 to 350 μs. Duty Cycle 1.0 to 2.0%.

(continued)

